

DOCKET NO: 263261US0PCT



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
HITOSHI KATO, ET AL. : EXAMINER: HARRISON, M. D.  
SERIAL NO: 10/518,025 :  
FILED: DECEMBER 15, 2004 : GROUP ART UNIT: 2813  
FOR: METHOD OF CVD FOR FORMING :  
SILICON NITRIDE FILM ON  
SUBSTRATE

AMENDMENT

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Responsive to the Office Action dated September 19, 2005, Applicants respectfully request reconsideration of the above-identified application in view of the following amendment and remarks.

**Amendments to the Claims** are reflected in the listing of claims which begins on page 2 of this paper.

**Discussion of the Amendment** begins on page 6 of this paper.

**Remarks** begin on page 7 of this paper.